L Number		- CAL		
1	47205	((force load stres strain weight) near 2 (1)	DB	Time stamp
		sens\$5 estimat\$5 evalut\$5 deterni\$5 measur\$5 transducer	USPAT:	2004/11/02 12:2
		cell meter gauge monitor\$5)).clm.	EPO; JPO	2004/11/02 12.2
3	287	(((IOrce load stres strain weight) ===== (1	
			USPAT;	2004/11/02 12:2
	1		EPO; JPO	1702 12.2
		bottom) near3 (electrode conduct\$5)).clm.		
	77	(\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\		
			USPAT;	2004/11/02 12:23
			EPO; JPO	
4				
	19	(((((force load stres strain weight) near3 (test\$5 detect\$5		
			USPAT;	2004/11/02 12:31
	1		EPO; JPO	
	-			
5	21			
	21	(((((IUICE IOAG Stres strain woight) o //	LICDAT	
			USPAT;	2004/11/02 12:32
			EPO; JPO	
6		Saporate, Citt. 1 800 Cabacité / Alm	1	
		(((((force load stres strain weight) near3 (test\$5 detect\$5	USPAT;	2004/44/00 45 5
			EPO; JPO	2004/11/02 12:34
			2. 0, 0, 0	
7	13	substrate.clm.) and ("n-type" "p-type")) and capacit\$7		
	Ì	((((((force load stres strain weight) near3 (test\$5 detect\$5	USPAT:	2004/11/02 12:35
		sens\$5 estimat\$5 evalut\$5 determin\$5 measur\$5 transducer cell meter gauge monitor\$5)).clm.) and ((upper lower top	EPO; JPO	2004/1/02 12.35
			·	
	s	semiconductor transistor)		
	(:	semiconductor transistor)	İ	
	14 ((((((force load stres strain woight) ====0 ((
			USPAT;	2004/11/02 12:35
			EPO; JPO	
	•	about die Citi.) did Capacits / clm \ and /aamin		
	tra	ansistor)	1	

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